BORN SEMICONDUCTOR

BAV23A / BAV23C / BAV23S

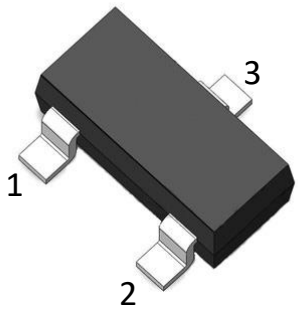
Fast Switching Diode

Features

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

Package

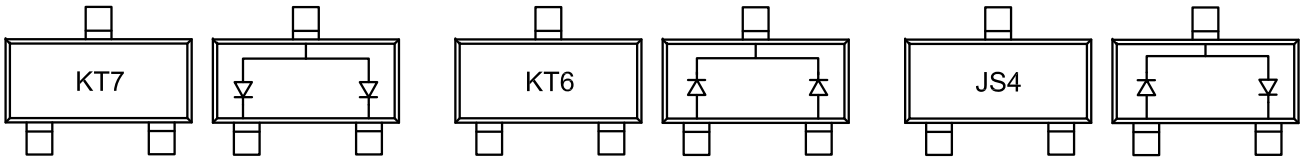
SOT-23



Description

- SOT-23 Small Outline Plastic Package
- Mounting Position: Any

Marking & Internal Wiring



BAV23A BAV23C BAV23S

Ordering information

Order code	Package	Marking	Base qty	Delivery mode
BAV23A	SOT-23	KT7	3K	Tape and reel
BAV23C	SOT-23	KT6	3K	Tape and reel
BAV23S	SOT-23	JS4	3K	Tape and reel

Maximum Ratings @T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Unit
V_{RRM}	Peak Repetitive Peak Reverse Voltage	250	V
V_{RWM}	Working Peak Reverse Voltage	175	V
I_O	Average Rectified Output Current	225	mA
I_{FRM}	Repetitive Peak Forward Surge Current	625	mA
I_{FSM}	Non-Repetitive Peak Forward Surge Current @t=8.3ms	1.7	A
P_d	Power Dissipation	350	mV
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	357	°C/W
T_J,T_{STG}	Operation Junction and Storage Temperature Range	-55 to +150	°C

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BAV23A / BAV23C / BAV23S

Fast Switching Diode

Electrical Characteristics @T_A=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Limits		Unit
			Min.	Max.	
V_R	Reverse Breakdown Voltage	I_R=100uA	250	–	V
I_R	Reverse Leakage Current	V_R=250V	–	0.1	uA
V_F	Forward Voltage	I_F=100mA	–	1.0	V
		I_F=200mA	–	1.25	
C_D	Diode capacitance	V_R=0V,f=1MHz	–	5	PF
T_{RR}	Reverse Recovery Time	I_F=I_R=30mA,I_{rr}=0.1XI_R,R_L=100Ω	–	50	nS

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BAV23A / BAV23C / BAV23S

Fast Switching Diode

Typical Performance Characteristics(T_J = 25 °C, unless otherwise noted)

Figure 1: Forward Characteristics

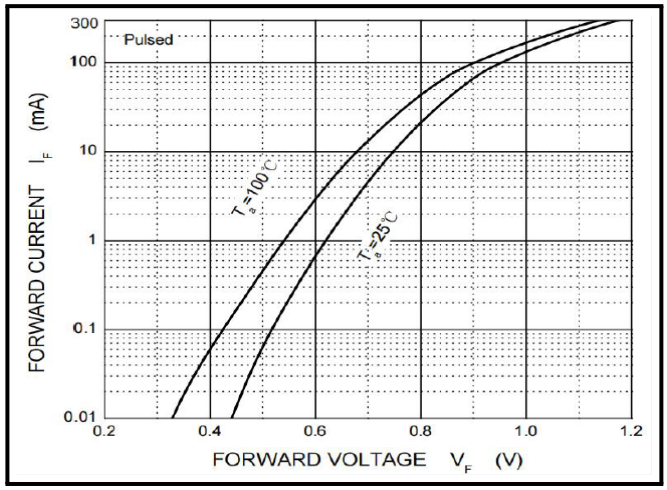


Figure 2: Reverse Characteristics

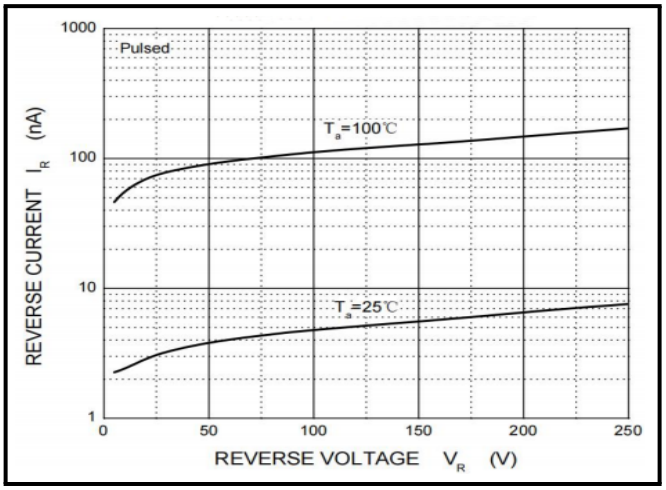


Figure 3: Capacitance Characteristics

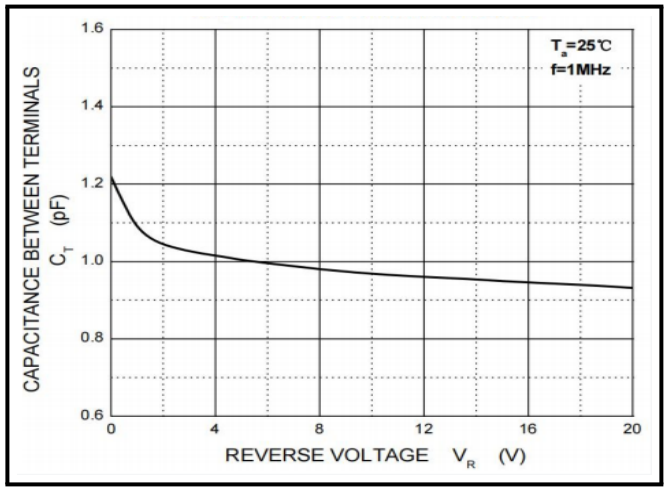
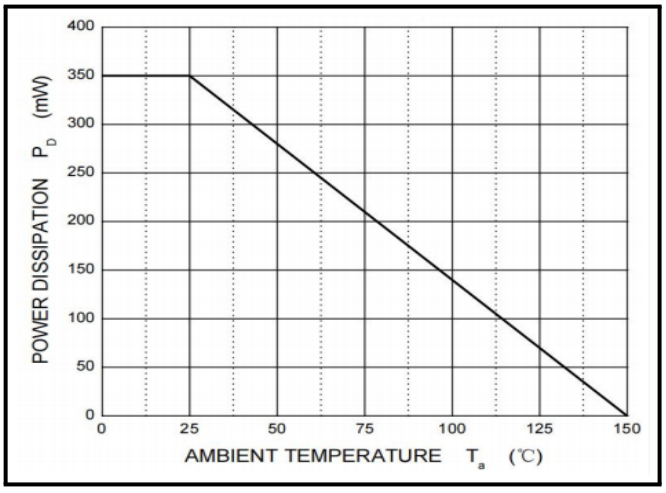


Figure 4: Power Derating Curve



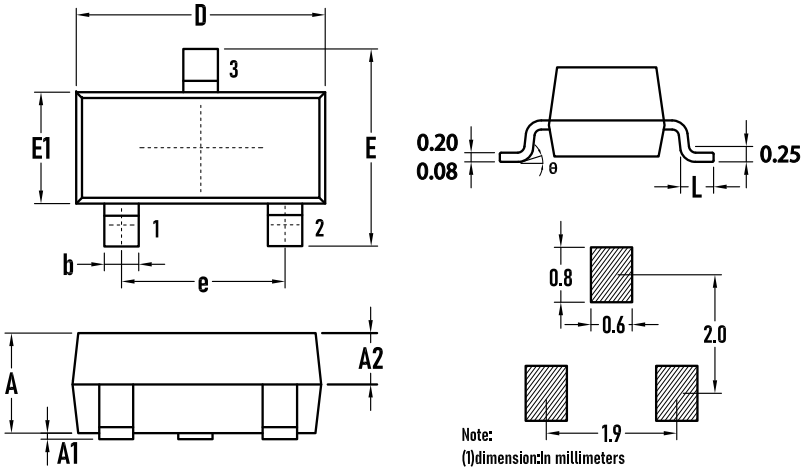
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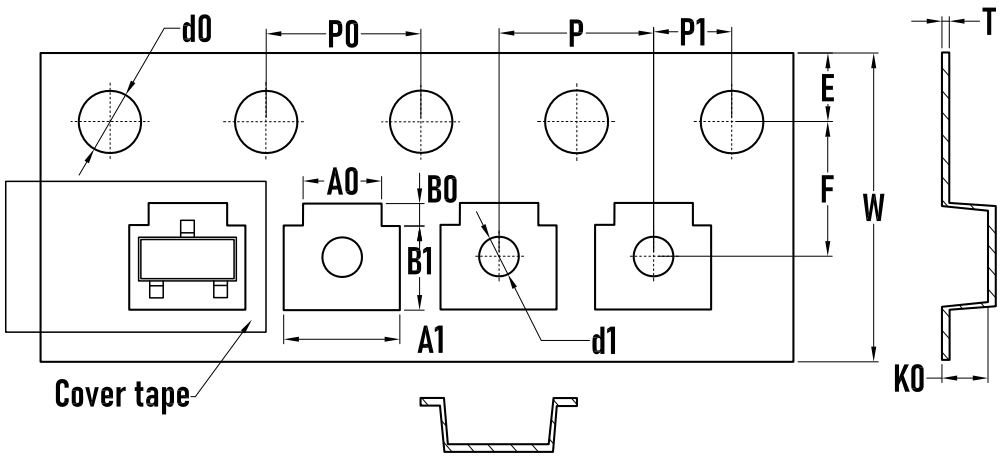
Fast Switching Diode

Outline Drawing - SOT-23



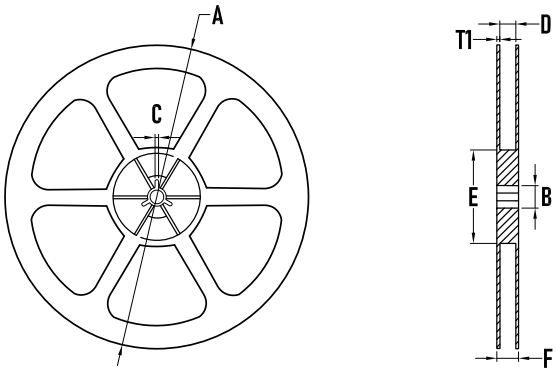
SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	0.90	1.00	1.10
A1	0.01	–	0.10
A2	0.50	0.60	0.70
D	2.80	2.90	3.00
b	0.25	0.35	0.45
E	2.10	2.30	2.50
E1	1.20	1.30	1.40
e	1.80	1.90	2.00
L	0.25	0.35	0.45
θ	0	–	8°

Packaging Tape - SOT-23



SYMBOL	MILLIMETER
A0	2.10±0.10
A1	3.10±0.10
B0	0.65±0.10
B1	2.75±0.10
d0	1.55±0.10
d1	1.00±0.05
E	1.75±0.10
F	3.50±0.10
K0	1.10±0.10
P	4.00±0.10
P0	4.00±0.10
P1	2.00±0.10
W	8.00±0.30
T	0.20 ±0.05

Packaging Reel



SYMBOL	MILLIMETER
A	177.8±0.2
B	3.1
C	13.50
D	9.6±0.3
E	75±0.2
F	12.3±0.3
T1	1.0±0.2
Quantity	3000PCS

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